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# **EUROPEAN PATENT APPLICATION**

21 Application number: **89104568.4**

51 Int. Cl.<sup>5</sup>: **H01L 29/78**

22 Date of filing: **15.03.89**

30 Priority: **18.03.88 JP 64960/88**  
**24.03.88 JP 69988/88**

43 Date of publication of application:  
**20.09.89 Bulletin 89/38**

84 Designated Contracting States:  
**DE FR GB**

88 Date of deferred publication of the search report:  
**23.05.90 Bulletin 90/21**

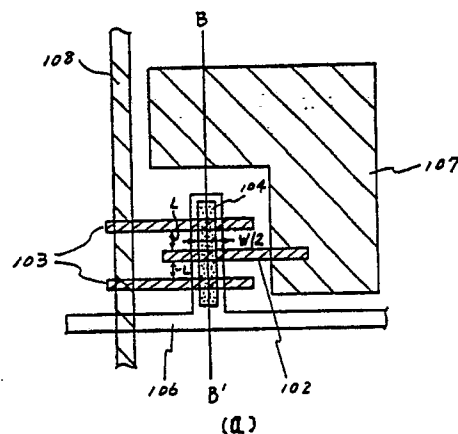
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54 **Thin film transistor.**

57 Described is a thin film transistor comprising on a substrate (101) a source electrode (103), a drain electrode (102), a semiconductor layer (104) contacting the source and drain electrodes, a gate insulating layer (105) and a gate electrode (106), wherein said source and drain electrodes (103, 102) are formed as parallel elongated strips extending in a first direction, said semiconductor layer (104) and said gate electrode (106) are formed as elongated strips extending in a second direction substantially perpendicular to said first direction, and said gate electrode (106) completely covering said semiconductor layer (104) through the gate insulating film (105). With this arrangement any shift of the gate electrode (106) with respect to source and drain electrodes (103, 102), which may occur during manufacturing, does not influence the parasitic capacitances between gate and source and gate and drain of the transistor. This ensures uniform transistor characteristics where a plurality of such thin film transistors are employed as for instance with an active matrix liquid crystal display device.



**FIG. 1**

**EP 0 333 151 A3**



DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl.4)
X	EP-A-0 200 138 (ASAHI GLASS CO. LTD) * Abstract; figures 2,11-14; column 6, line 48 - column 7, line 49 *	1,2	H 01 L 29/78 G 02 F 1/133
Y	---	1,2	
X	EP-A-0 216 673 (THOMSON-CSF) * Abstract; figure 9 *	1	
Y	---		
Y	FR-A-2 599 559 (GENERAL ELECTRIC CO.) * Abstract; figure 4; page 6, line 35 - page 7, line 16 *	1,2	
A	---		
A	EP-A-0 209 113 (GENERAL ELECTRIC CO.) * Abstract; figures 3A-3C; figure 5; page 9, line 23 - page 11, line 33 *	1,2	
A	---		
A	PATENT ABSTRACTS, vol. 10, no. 289 (E-442)[2345], 2nd October 1986; & JP-A-61 108 171 (TOSHIBA CORP.) 26-05-1986 * Whole document *	1	
			TECHNICAL FIELDS SEARCHED (Int. Cl.4)
			H 01 L
The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 28-02-1990	Examiner MIMOUN B.J.
<b>CATEGORY OF CITED DOCUMENTS</b> X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons ..... & : member of the same patent family, corresponding document			